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図 1 A

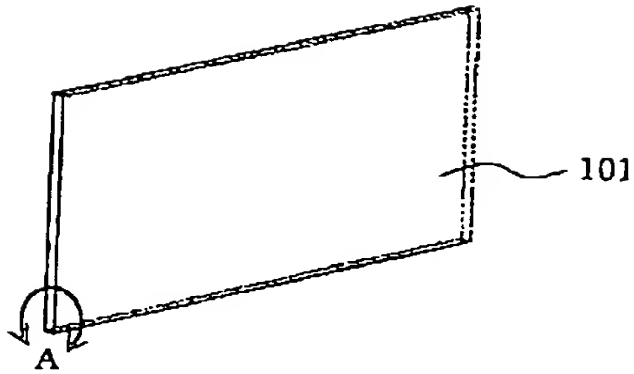


図 1 B



A部詳細

図 1 C

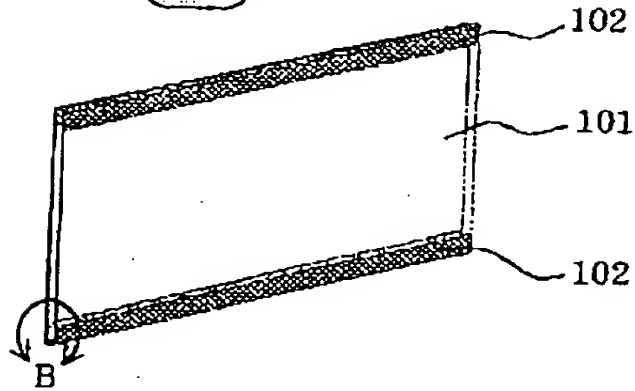
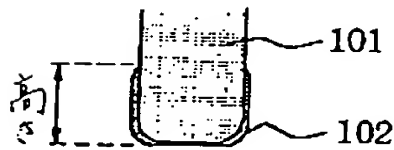
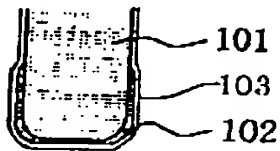


図 1 D



B部詳細

図 1 E



09505627.021600

図 2 A

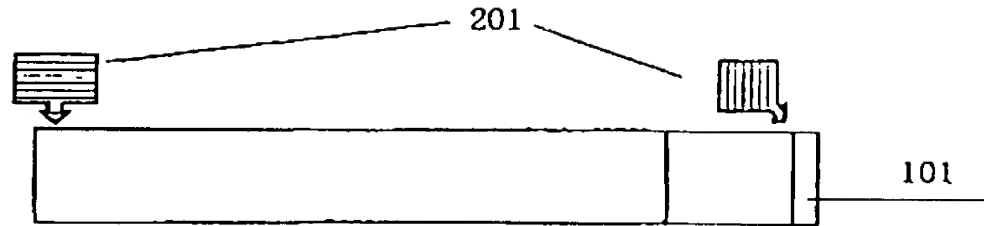


図 2 B

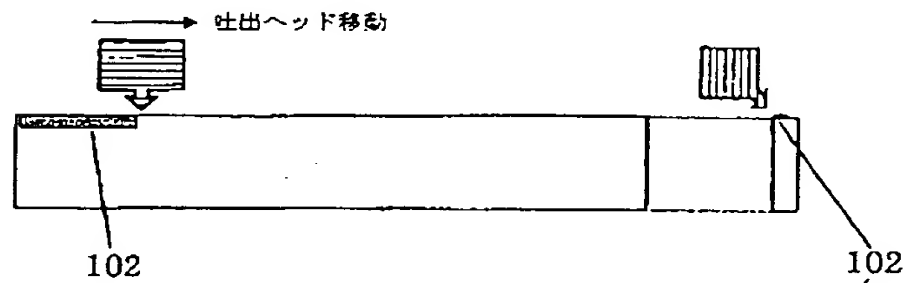


図 2 C

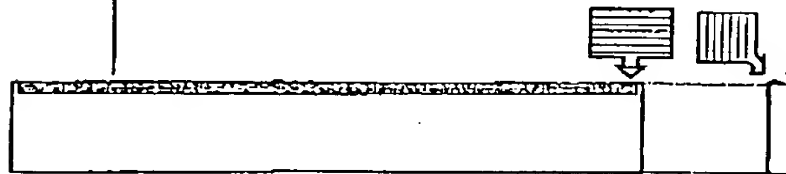


図 2 D

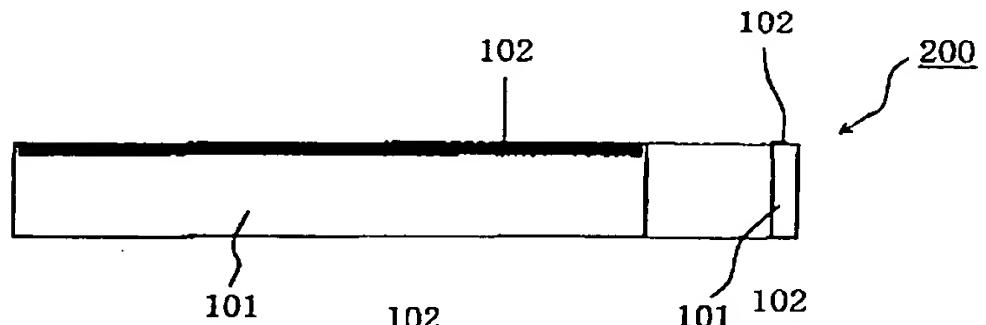
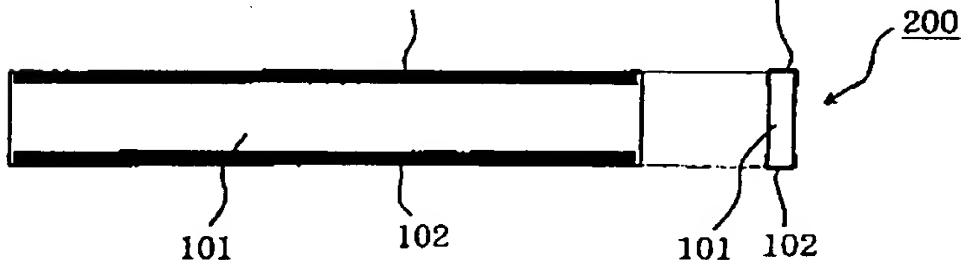


図 2 E



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图 3 A

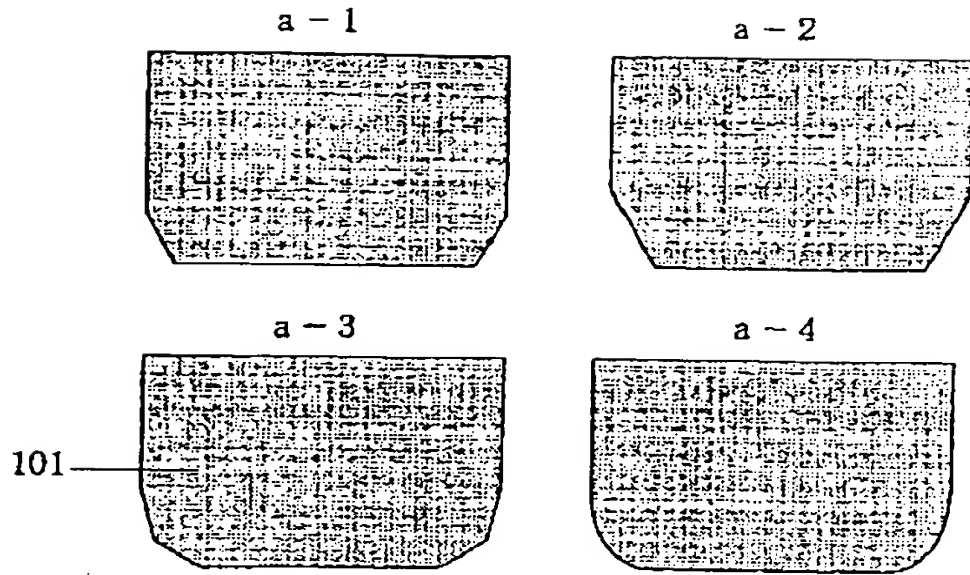
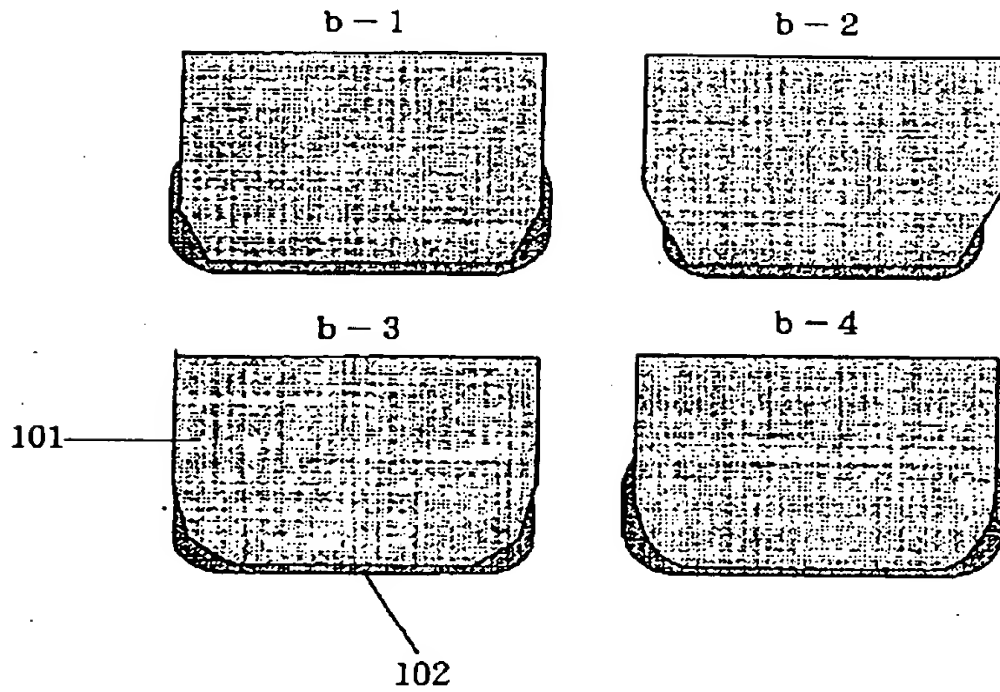
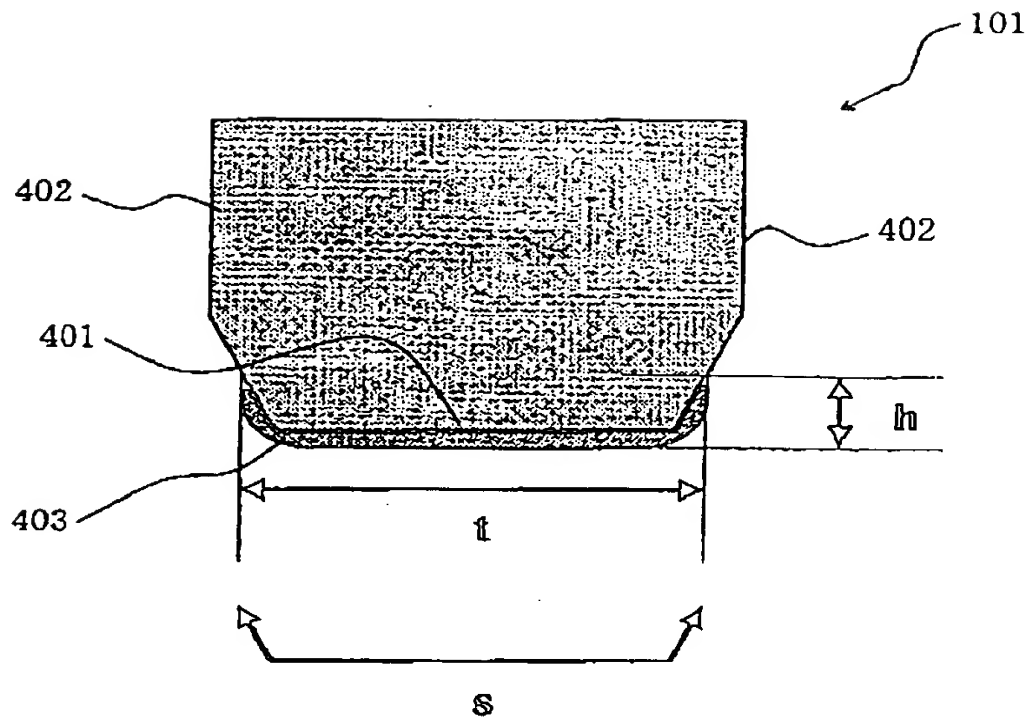


图 3 B



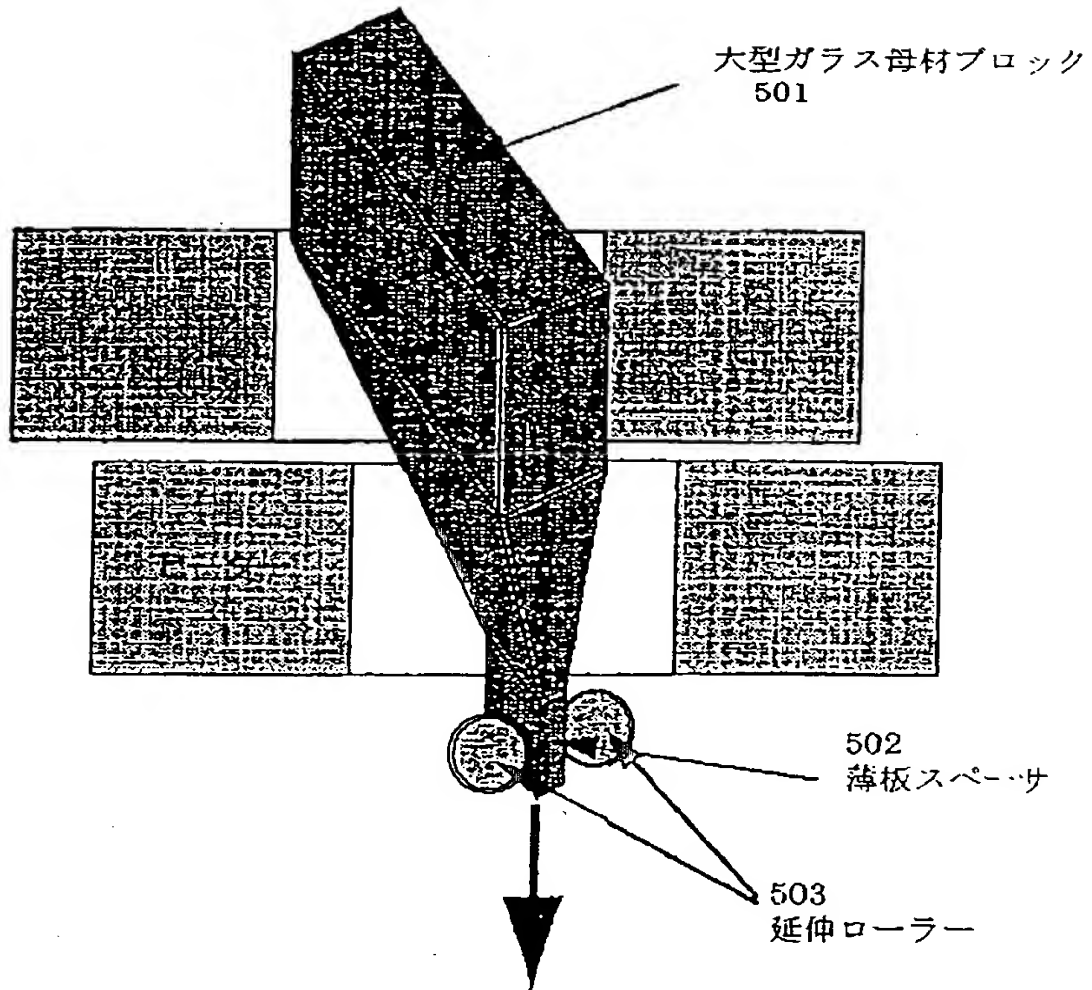
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図 4



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図 5



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吐出ヘッド移動

図 6 A

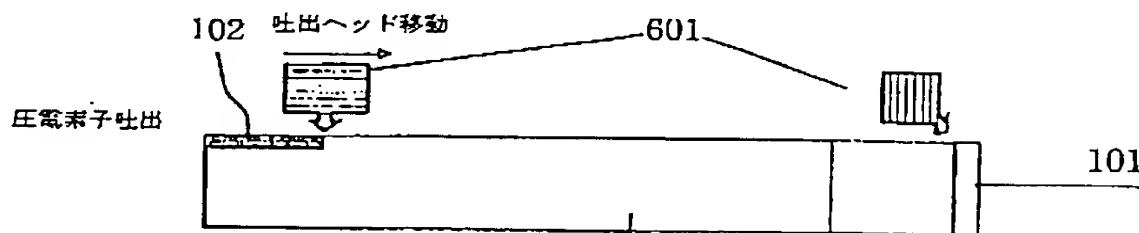


図 6 B

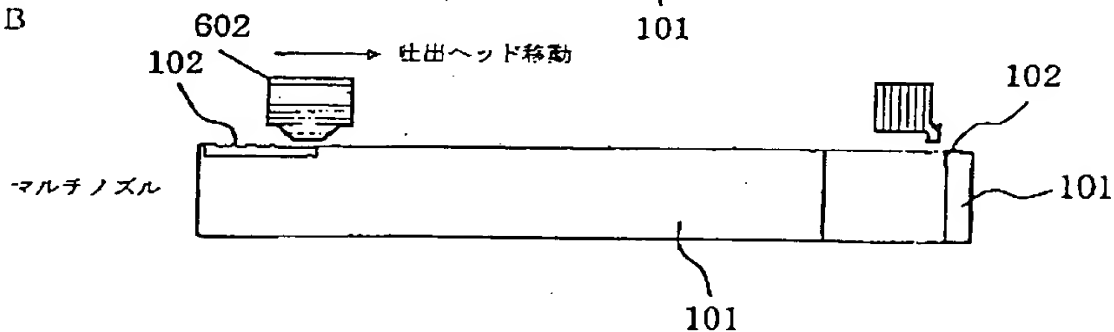
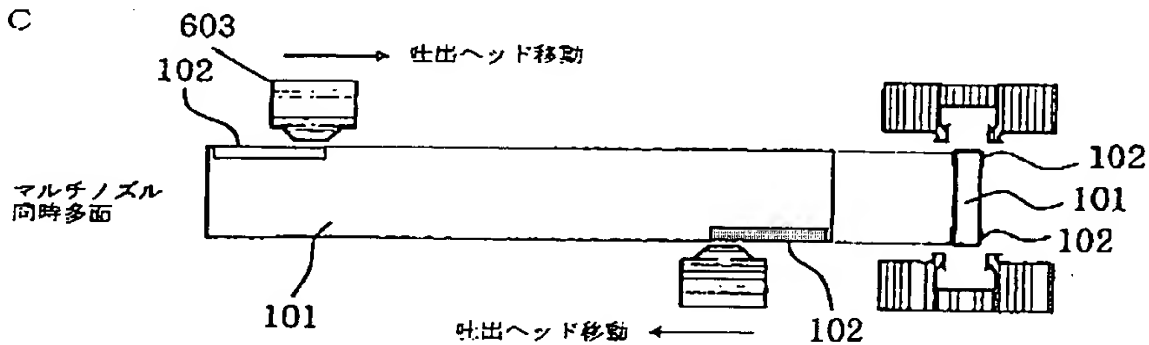
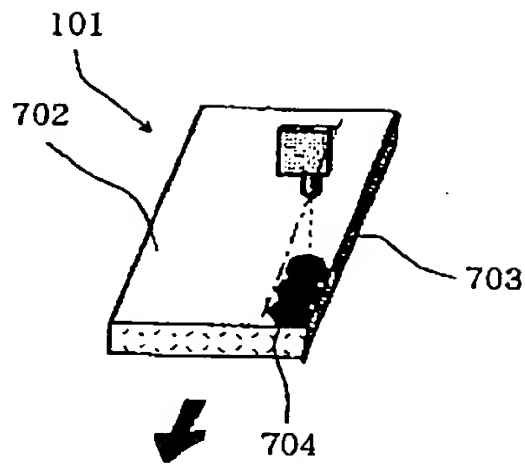


図 6 C



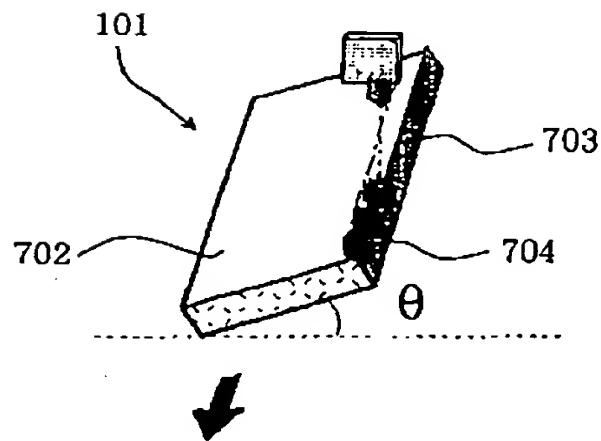
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図 7 A



垂直打ち(平置き)

図 7 B



斜め打ち(傾斜)
側面、底面同時形成

図 8 A

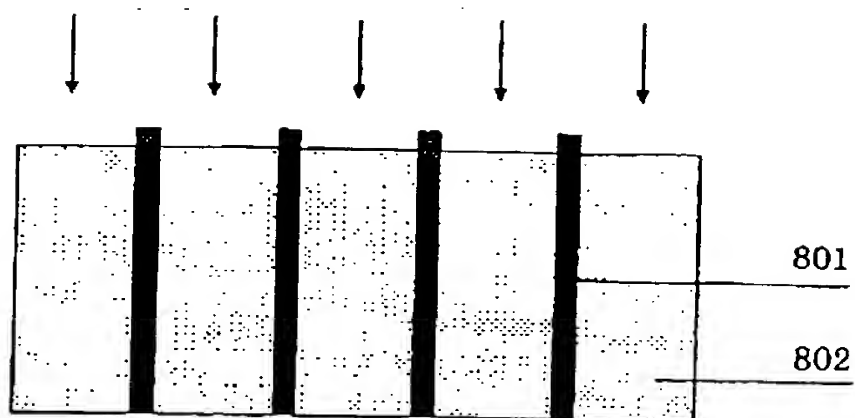


図 8 B

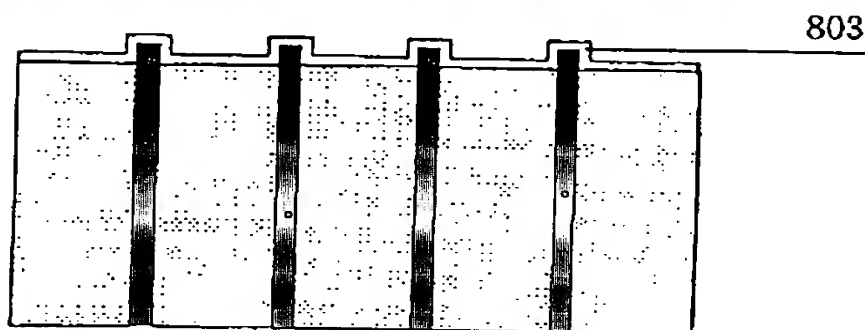


図 8 C

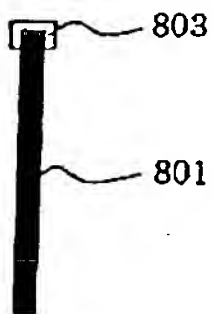
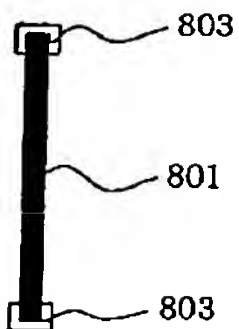


図 8 D



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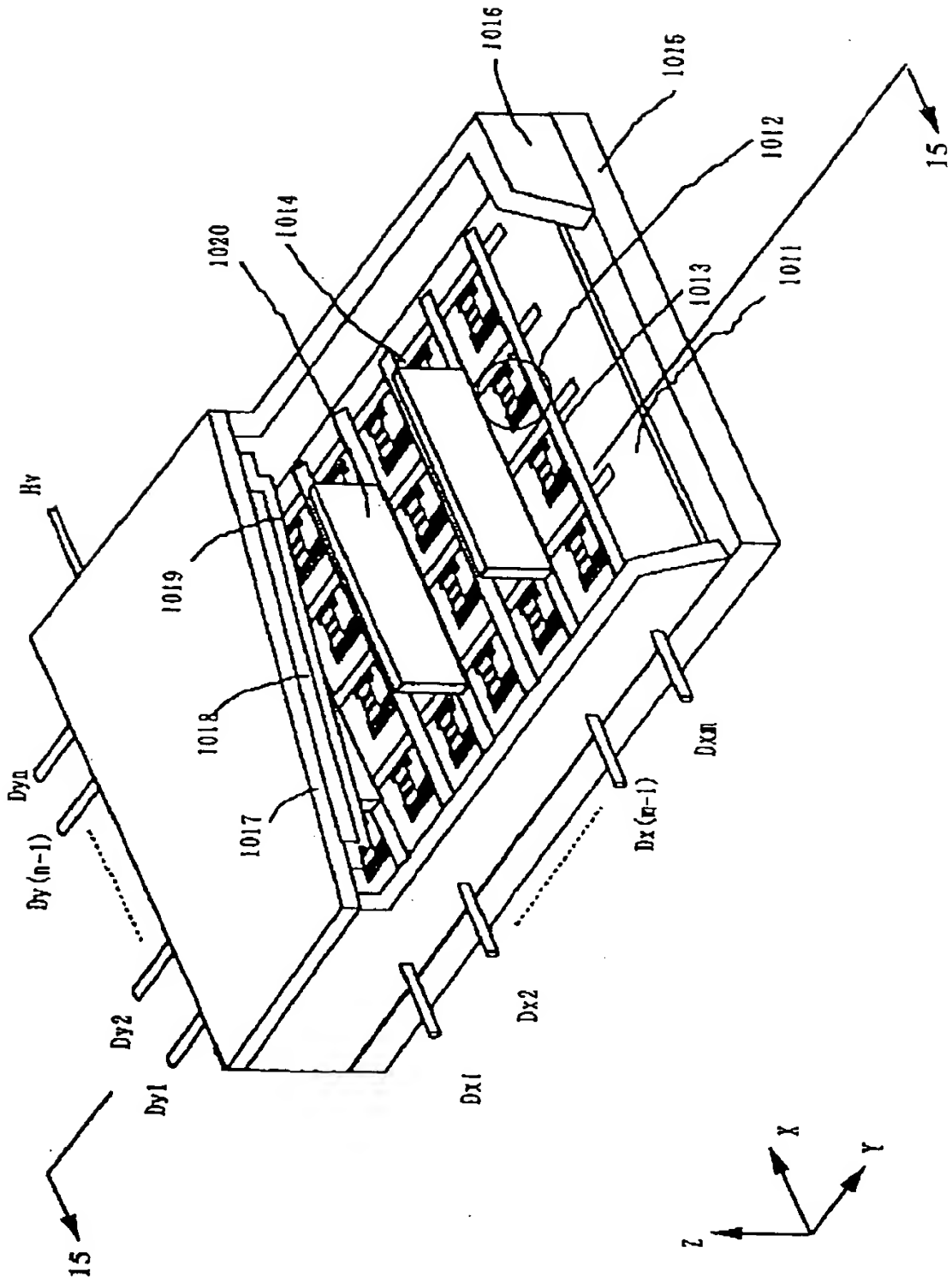
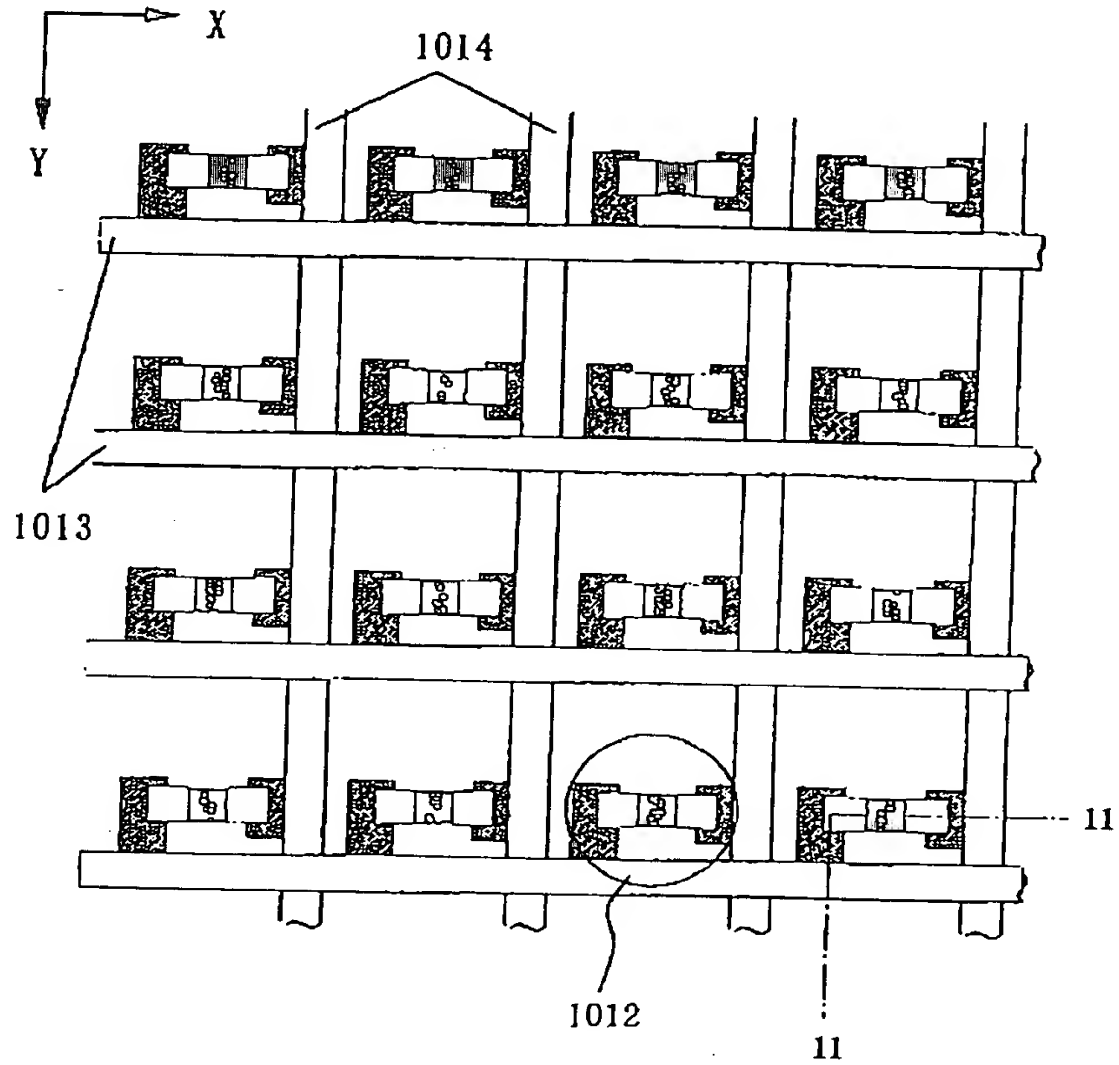


图 10



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Figure 1 is a schematic diagram of the structure of the light-emitting device. It shows a series of vertical bars representing the device structure. The bars are labeled R, G, B, R, G, B from left to right. A coordinate system is shown at the top left with X and Y axes. A label "黑色導電材 1010" (Black conductive material 1010) points to the top of the bars. A legend at the bottom right defines the colors: R: 赤色螢光体 (Red phosphor), G: 綠色螢光体 (Green phosphor), B: 青色螢光体 (Blue phosphor).

図 13

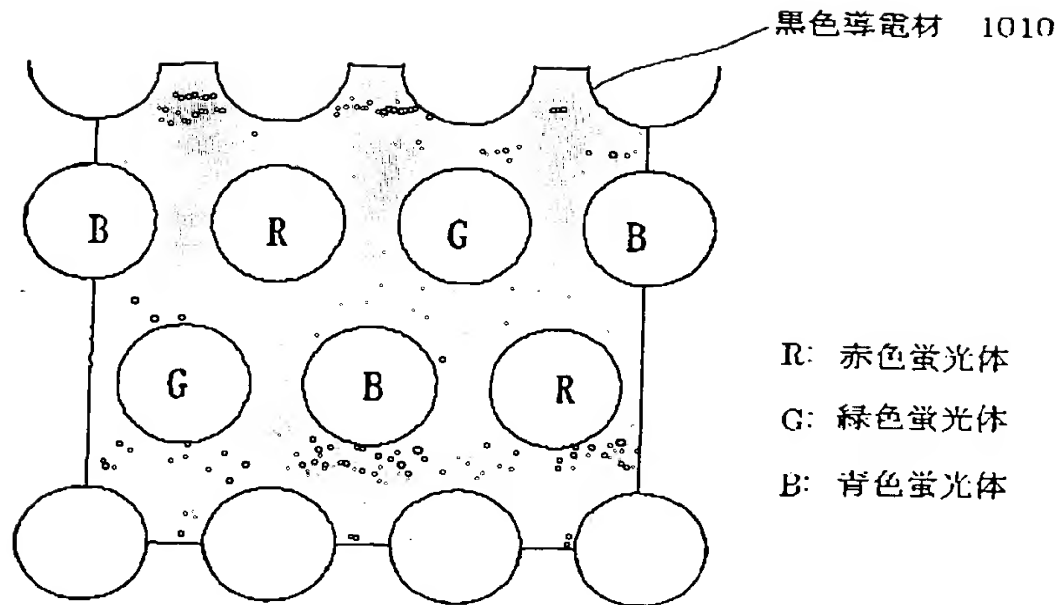
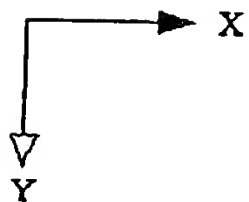
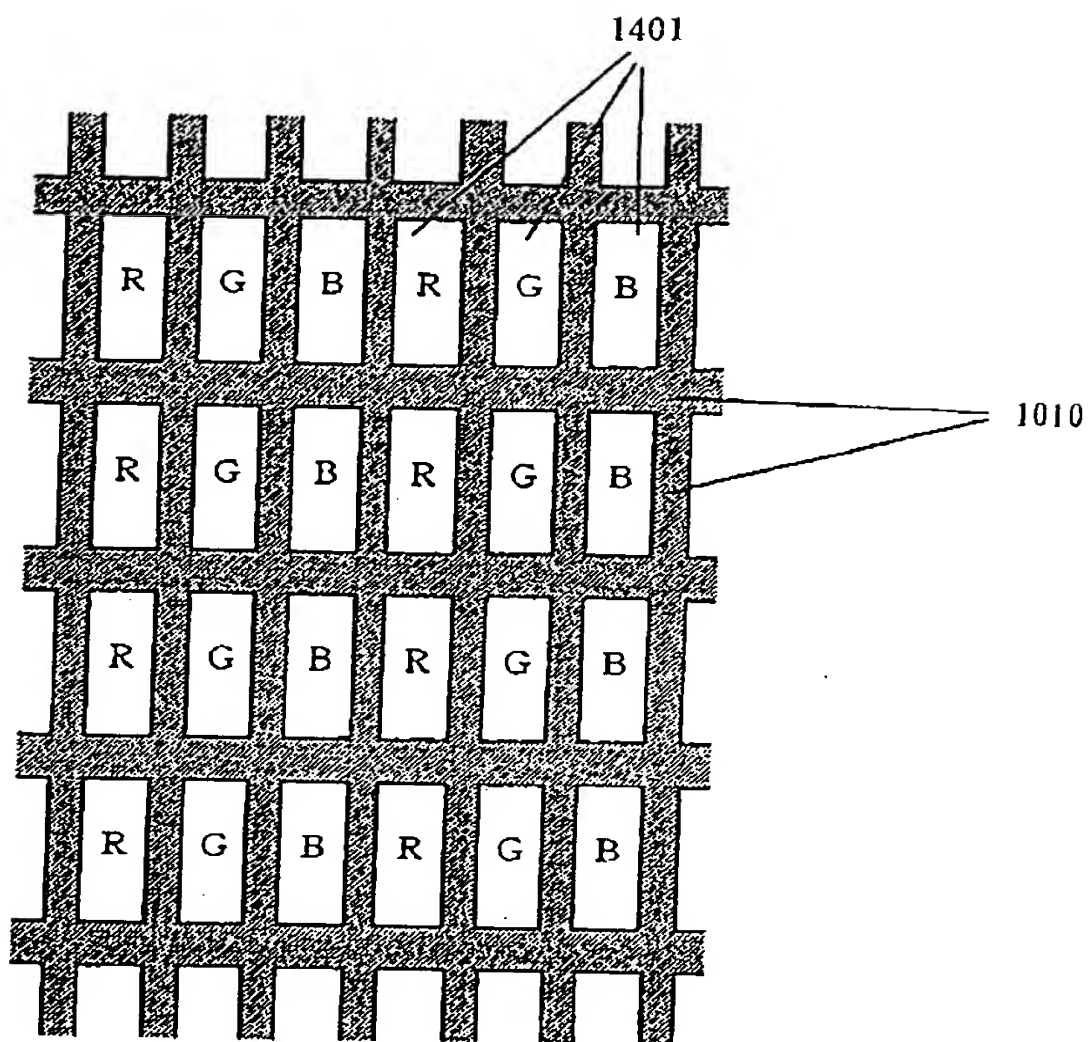
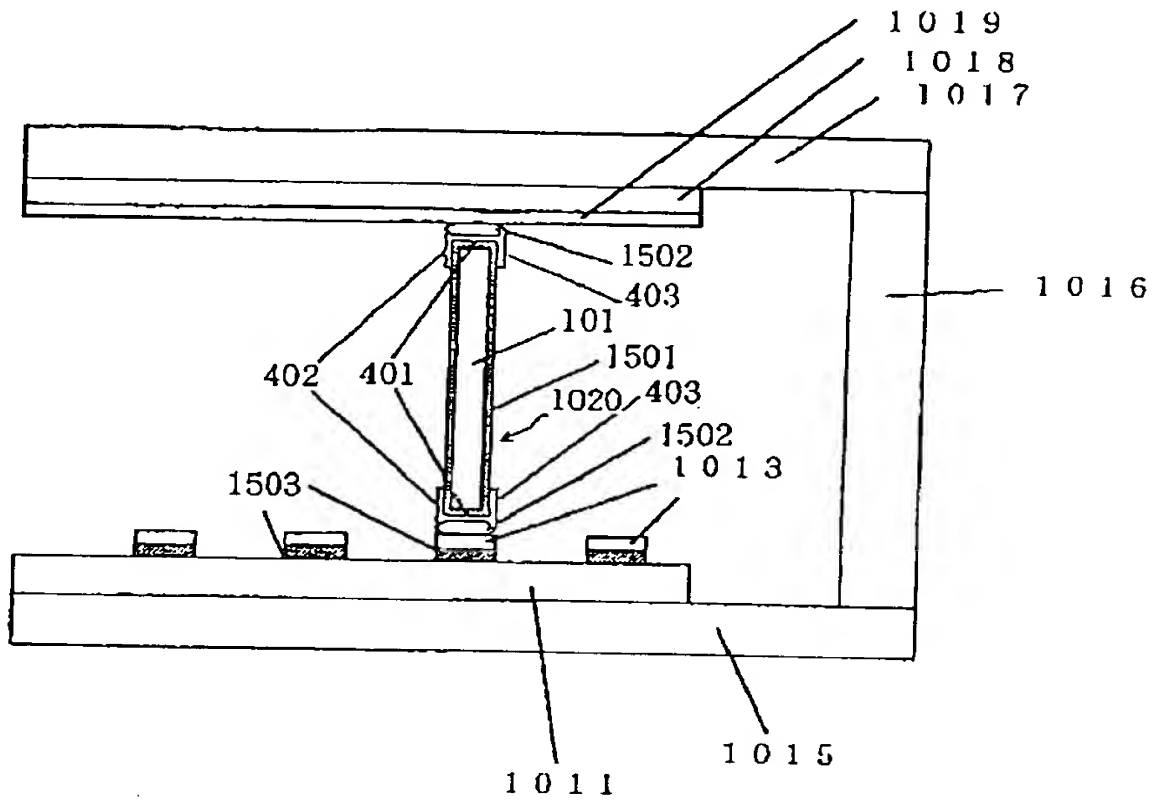


图 14



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图 15



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図 16 A

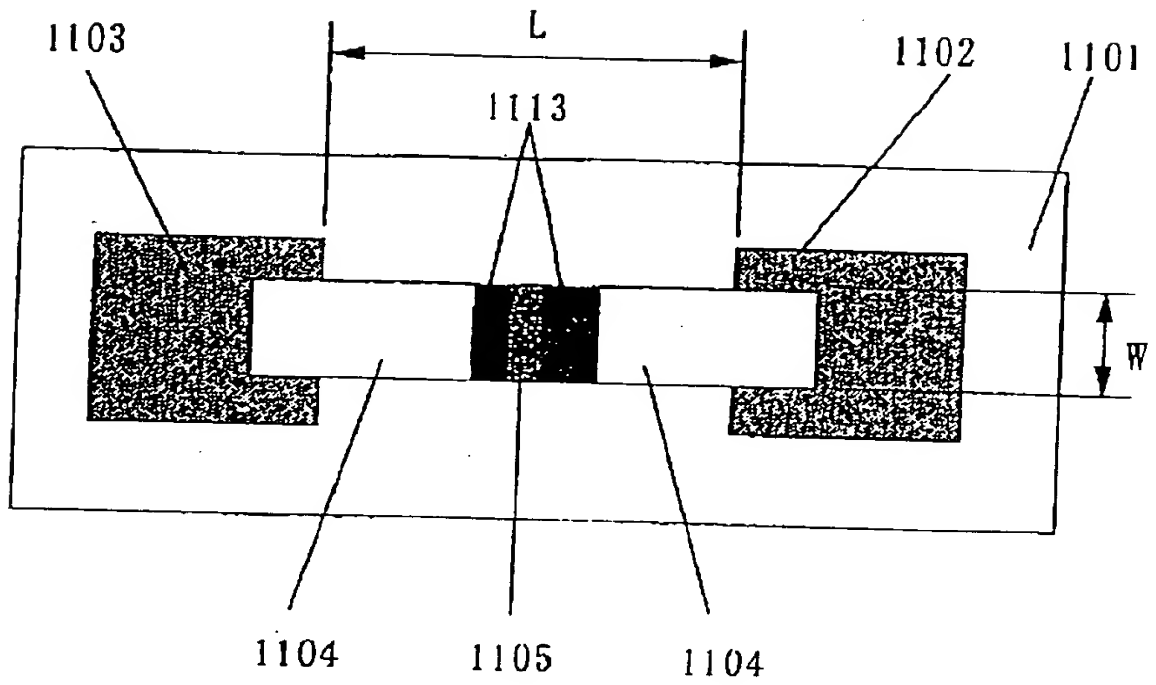
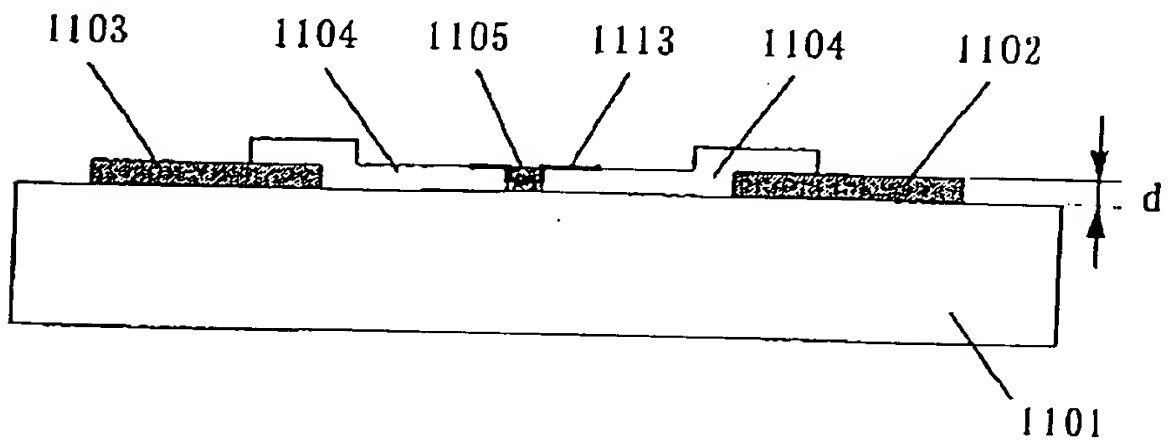


図 16 B



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图 17 A

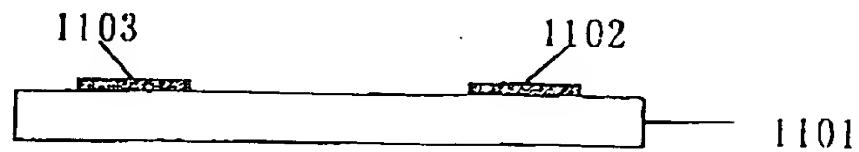


图 17 B

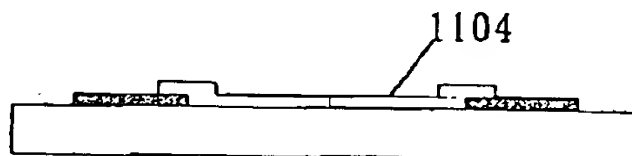


图 17 C

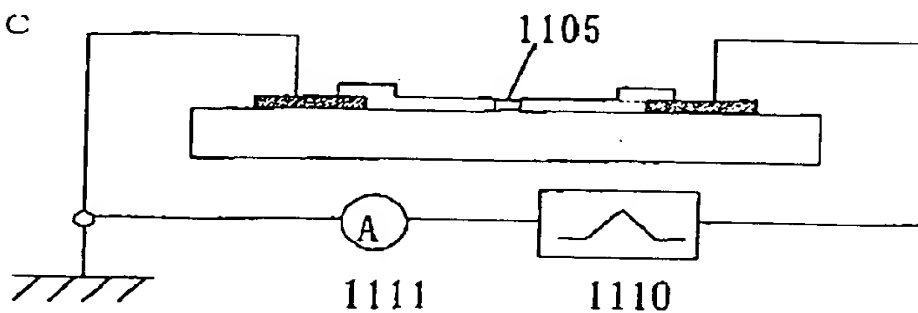


图 17 D

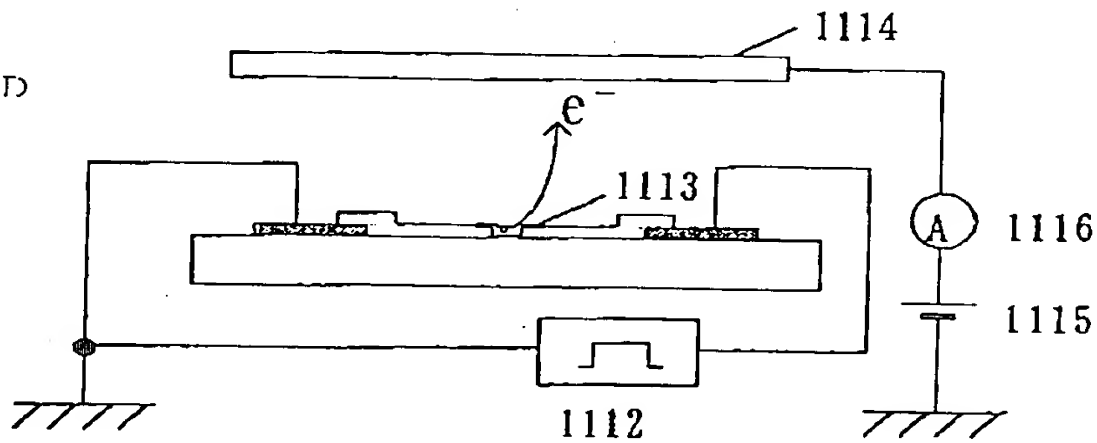


图 17 E

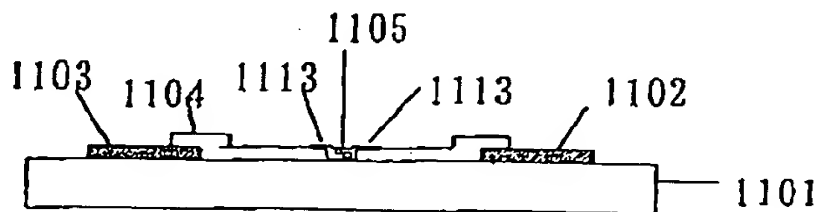
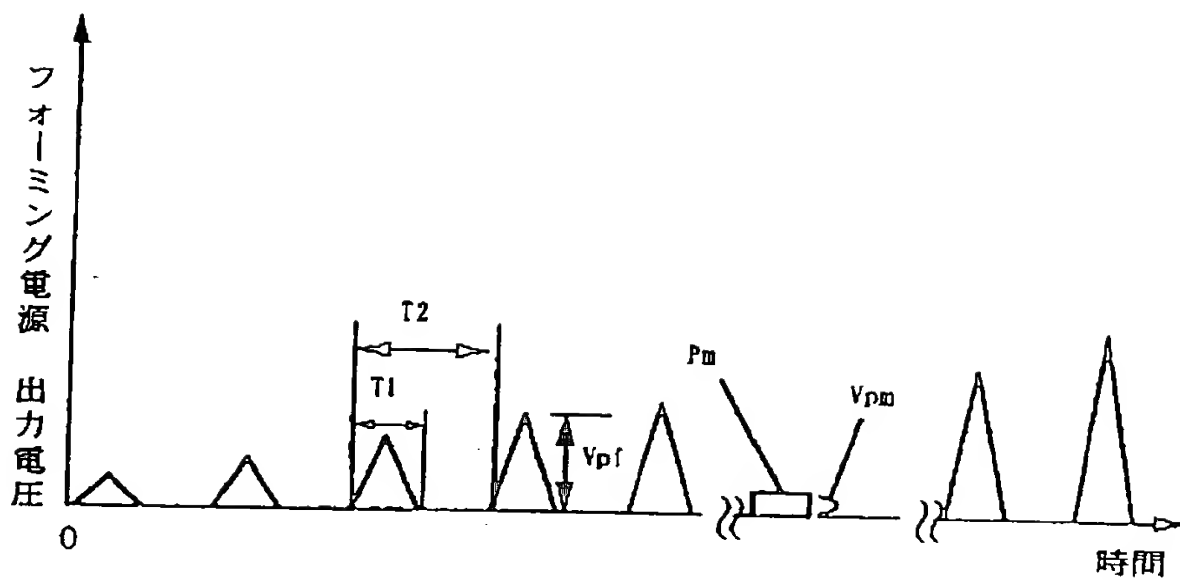


図 18



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図 19 A

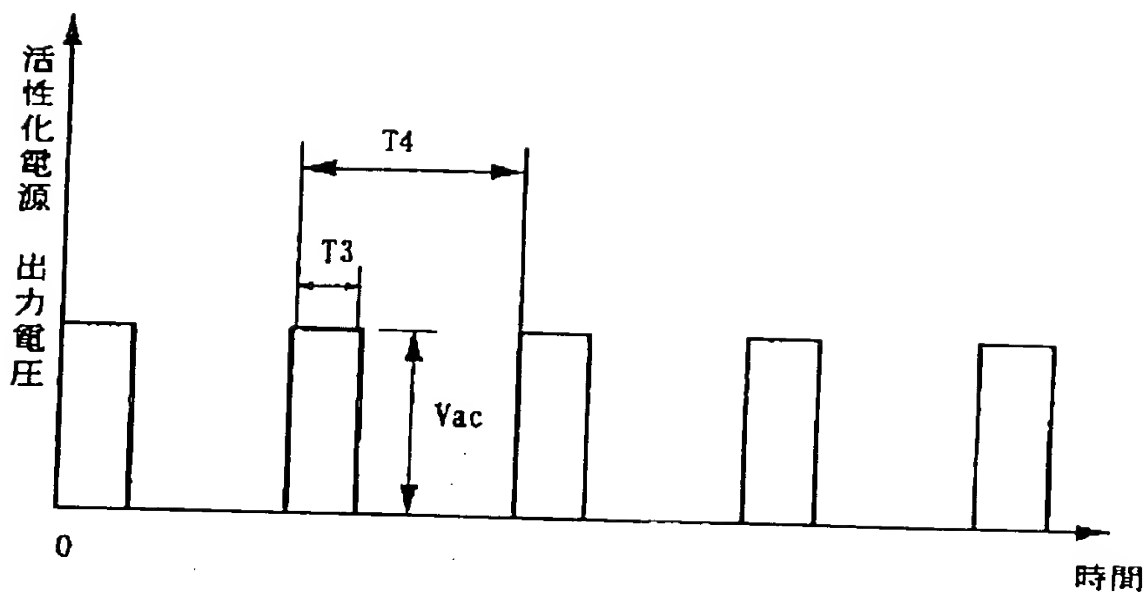
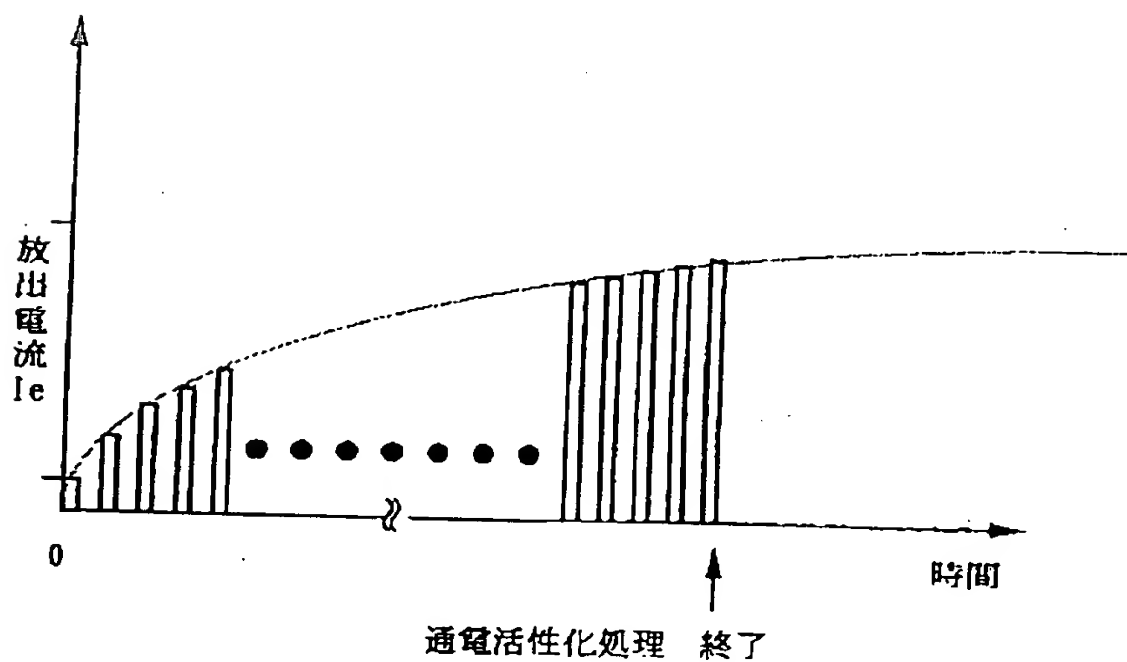
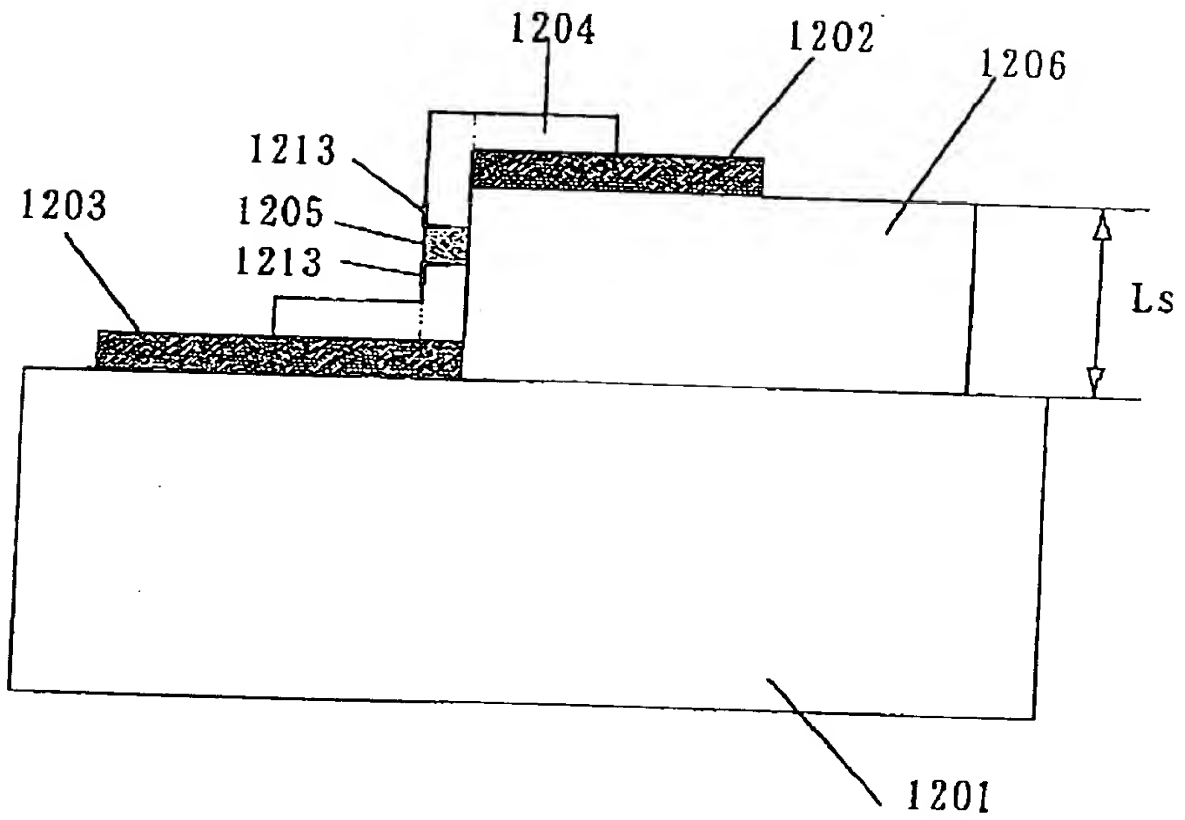


図 19 B



20



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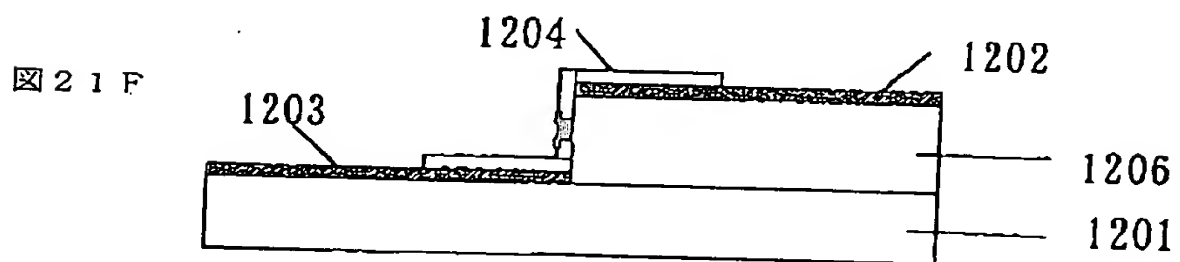
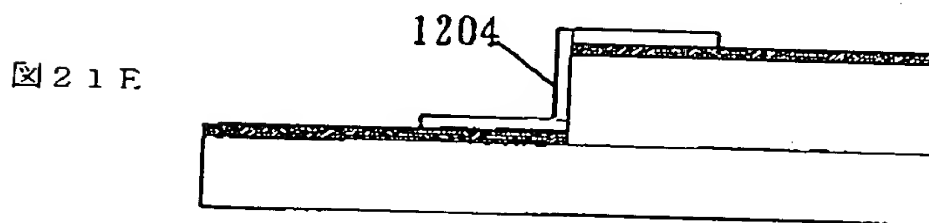
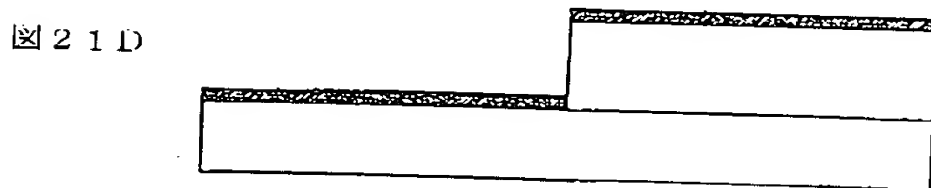
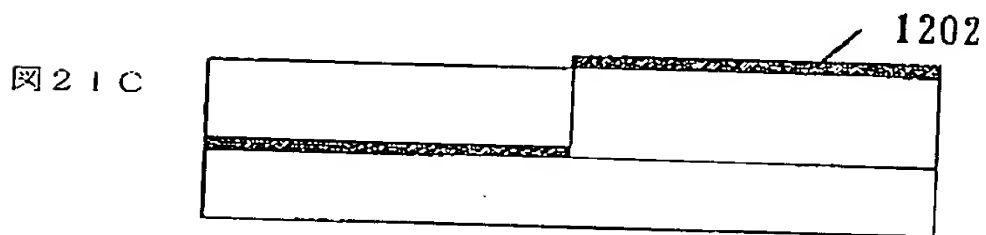
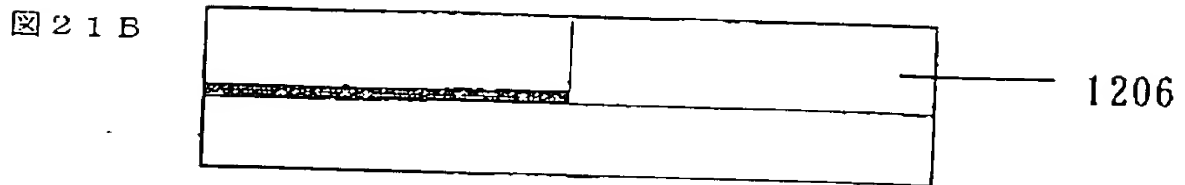
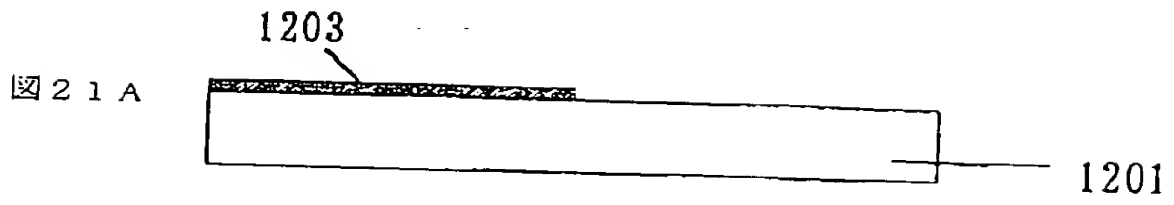
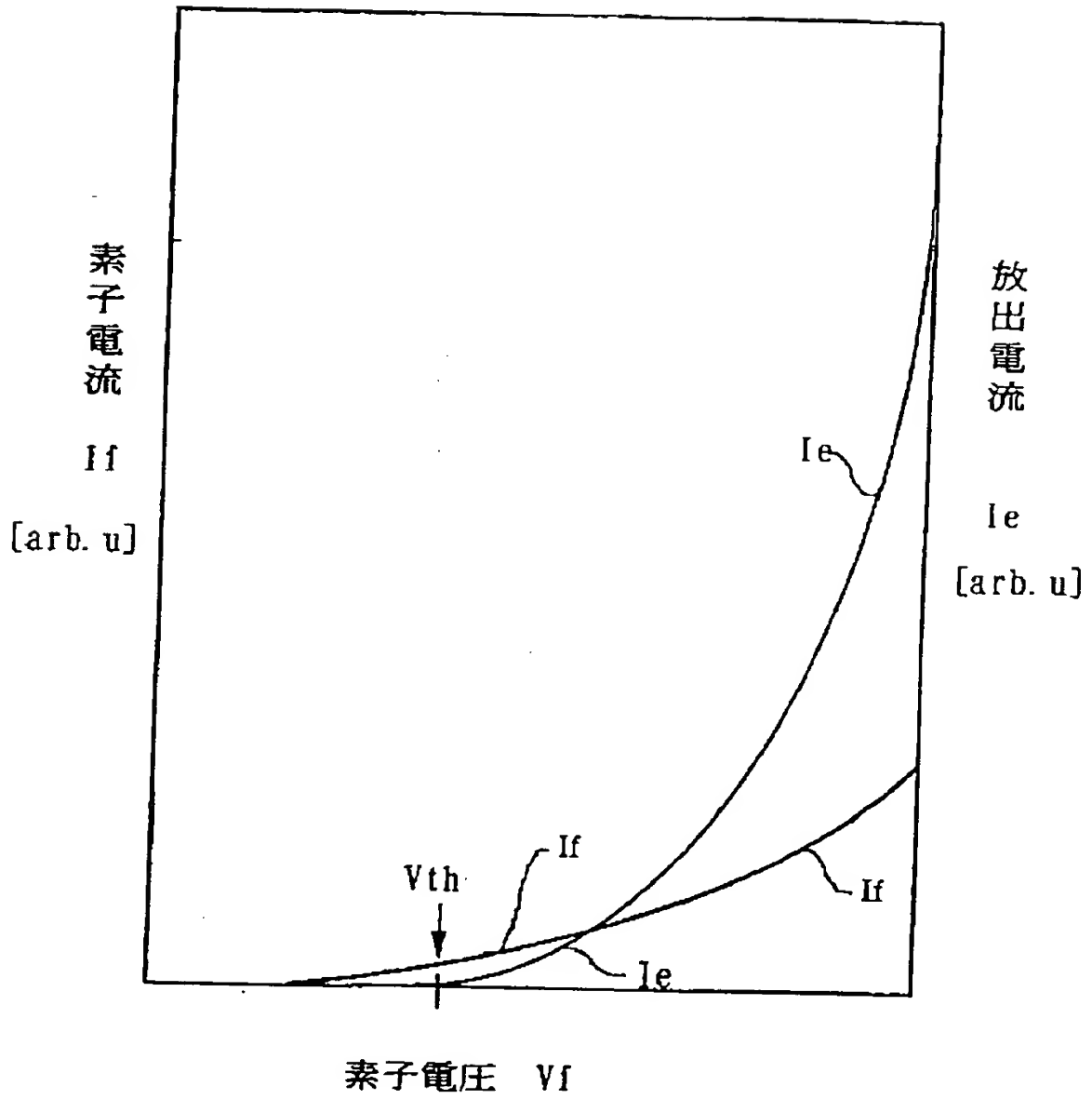
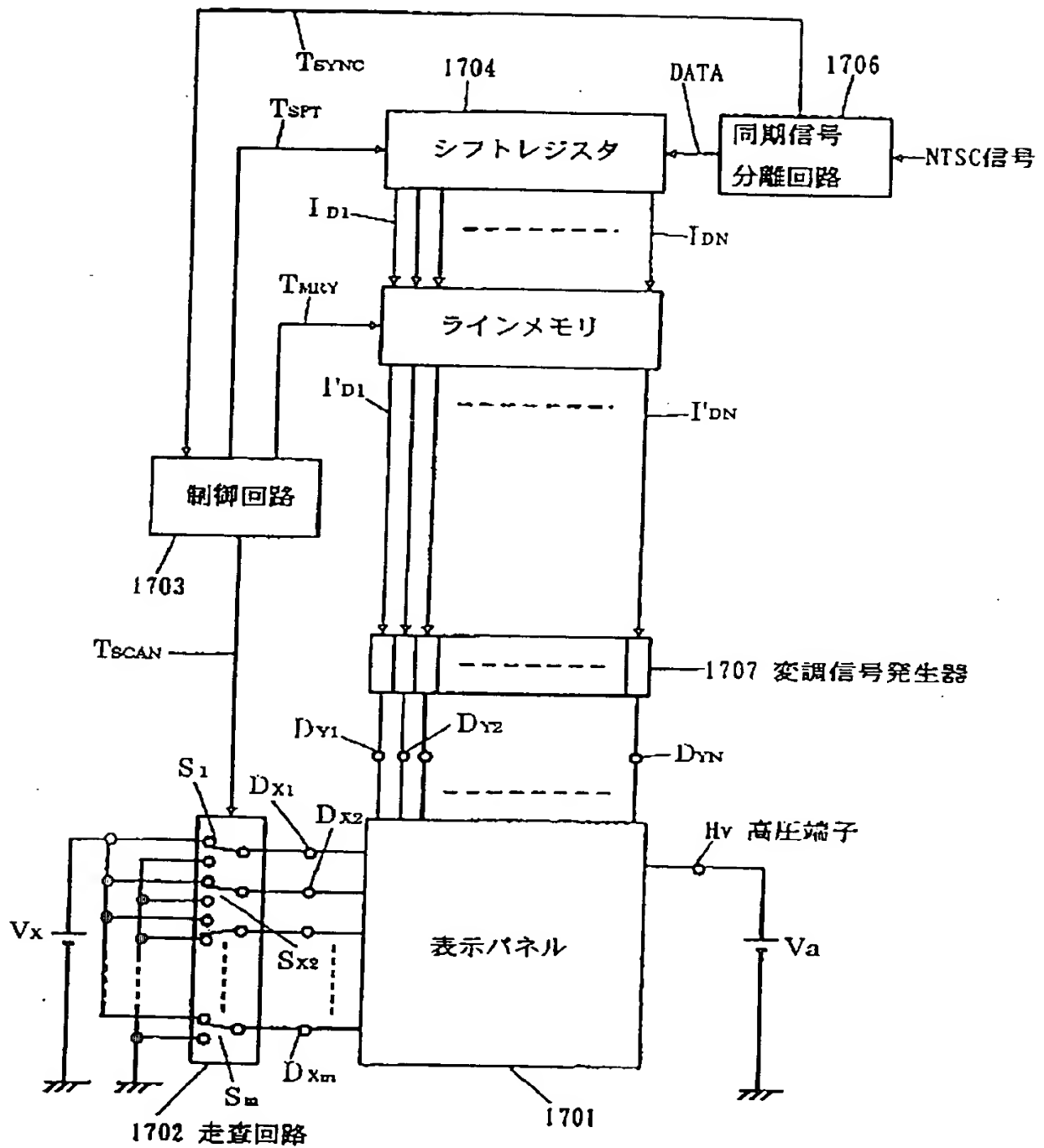


図 2 2



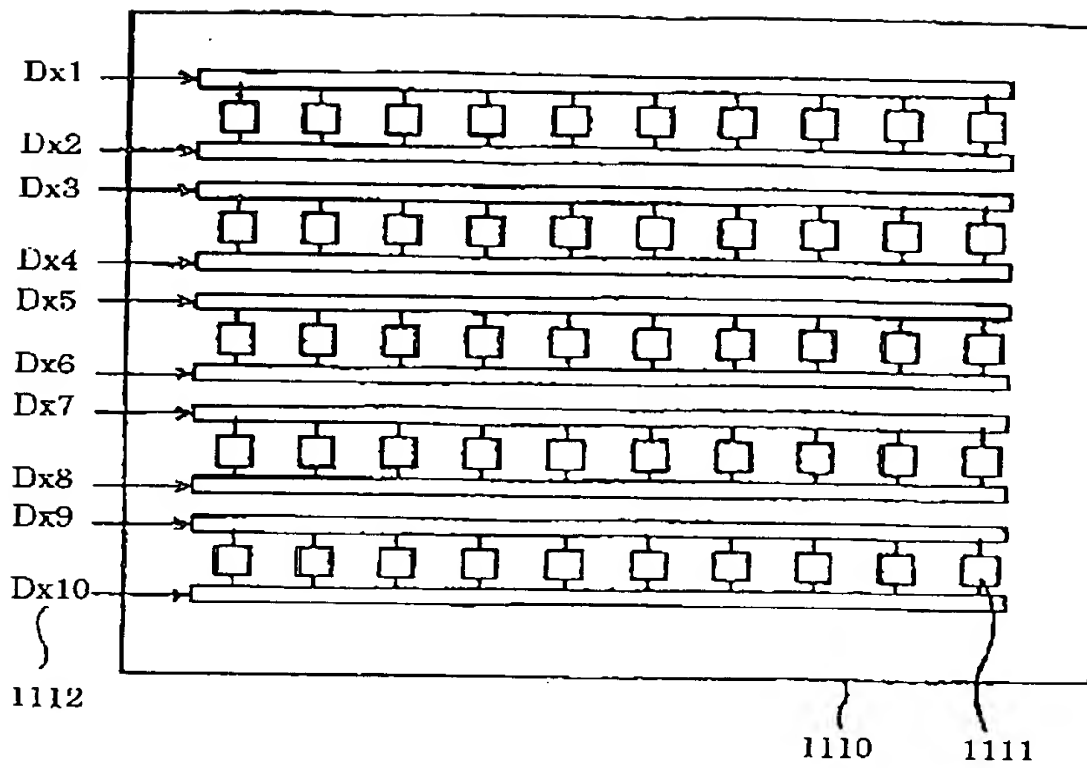
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図 23



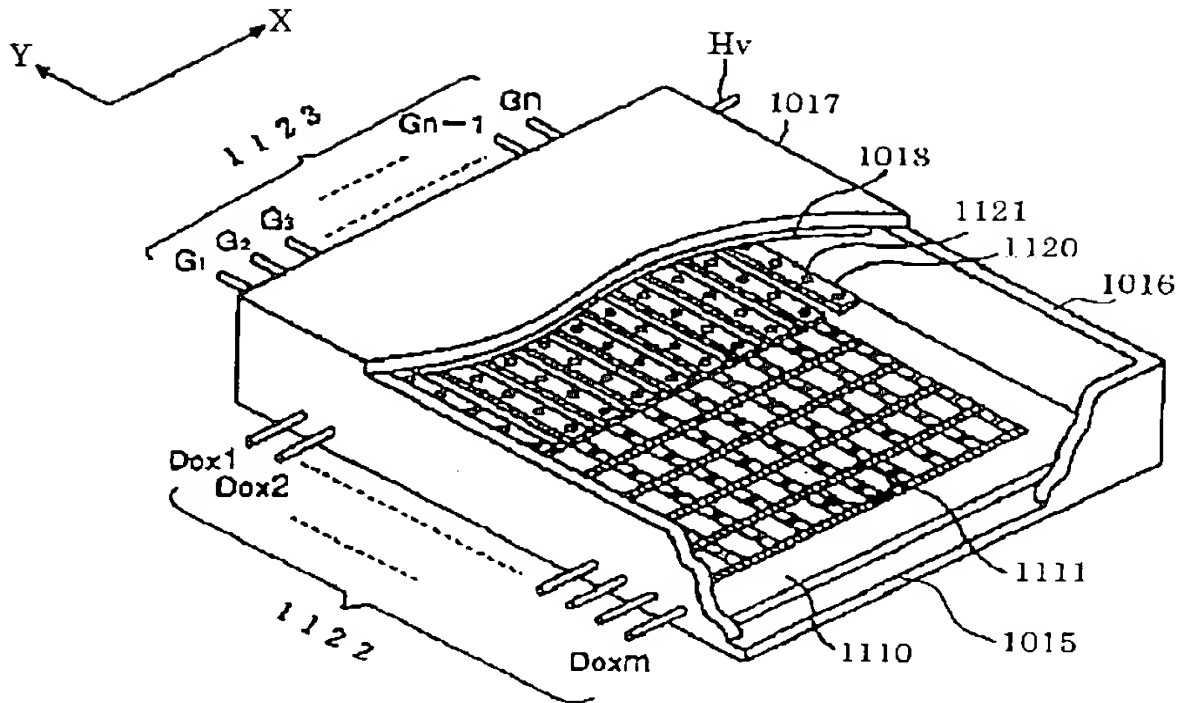
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図 24



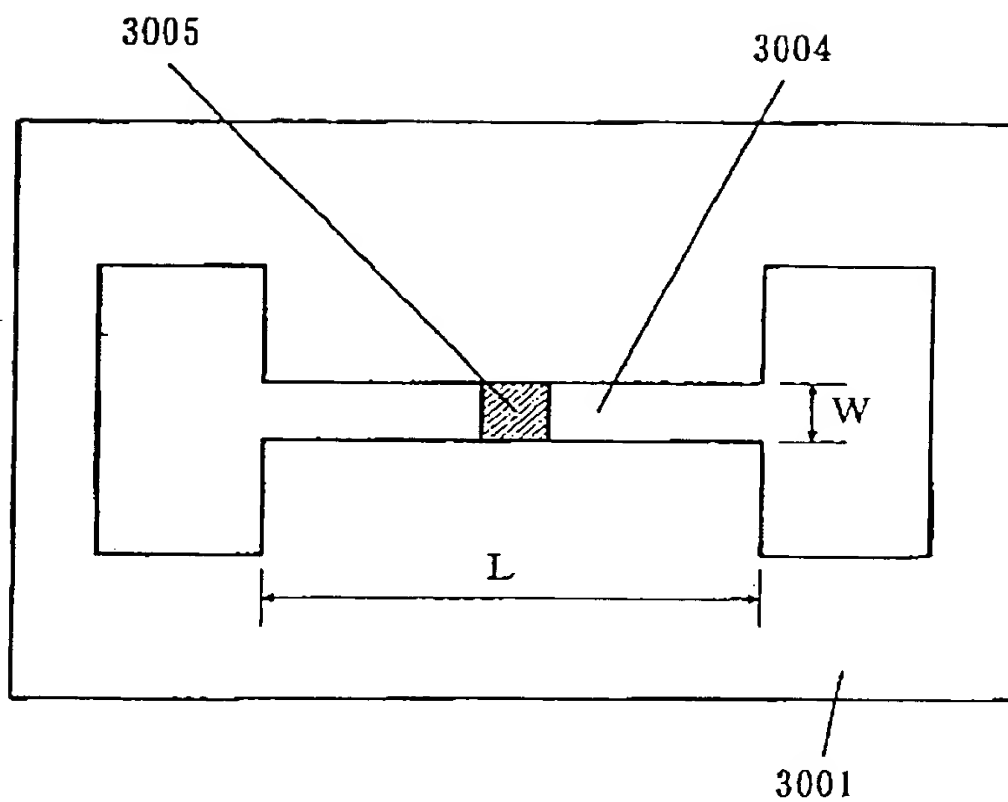
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Figure 25 is a 3D perspective view of a semiconductor device structure. The device is shown in a perspective view with X and Y axes. The structure includes a substrate with a grid of elements. Labels include: X and Y axes; G1, G2, G3, Gn-1, Gn (gate electrodes); Hv (hole voltage); 1017, 1018, 1016, 1015 (structural layers); 1123, 1122, 1121, 1120 (interconnects); Dox1, Dox2, Doxm (drain electrodes); and 1111, 1110 (channel regions).



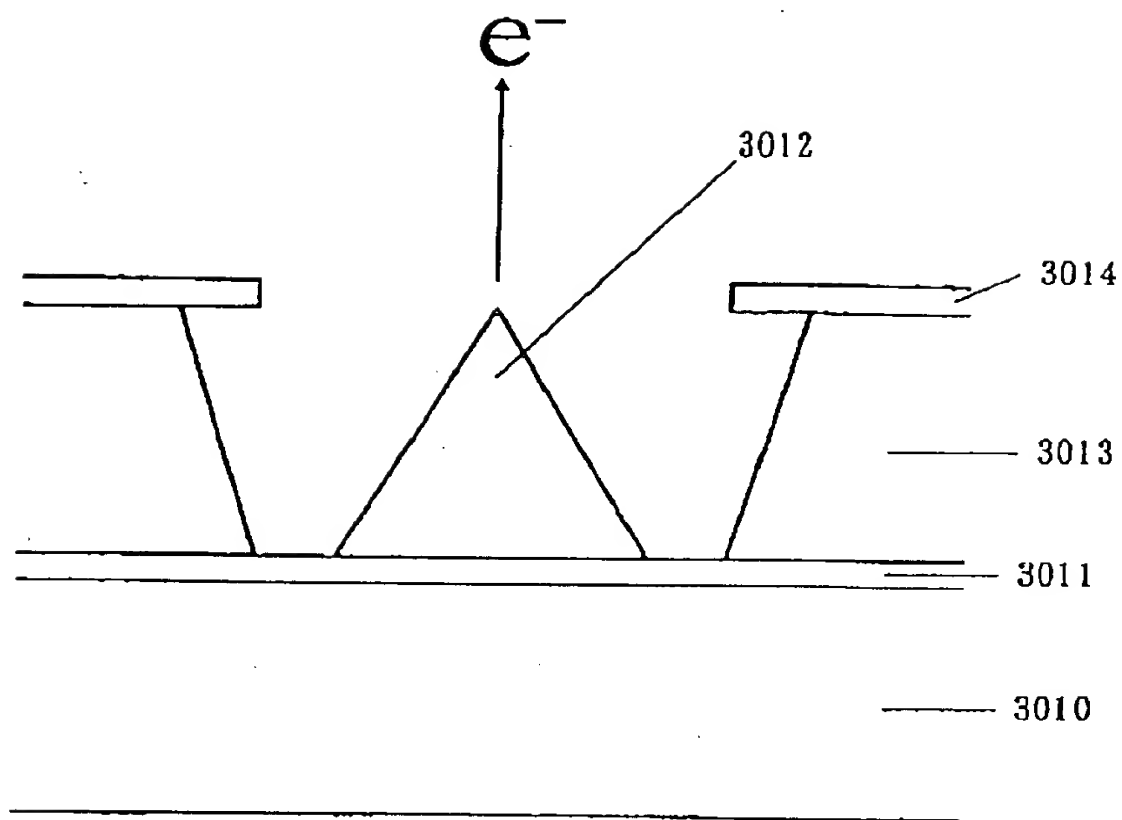
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图 2 6



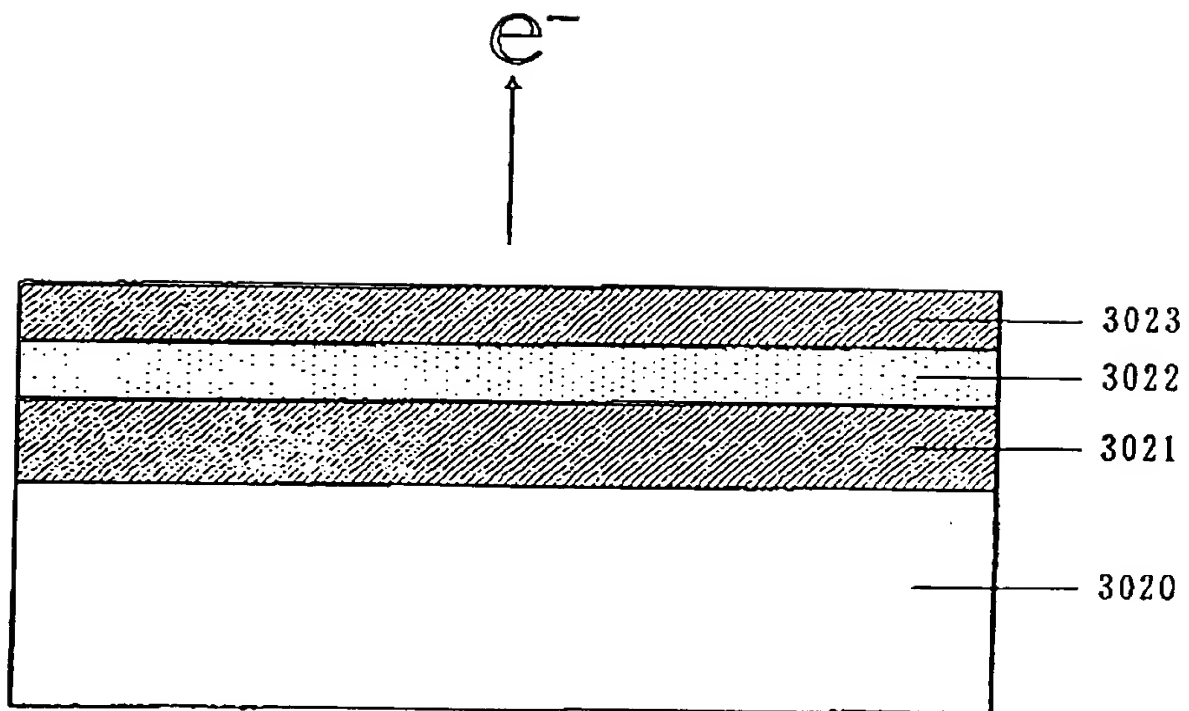
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图 27



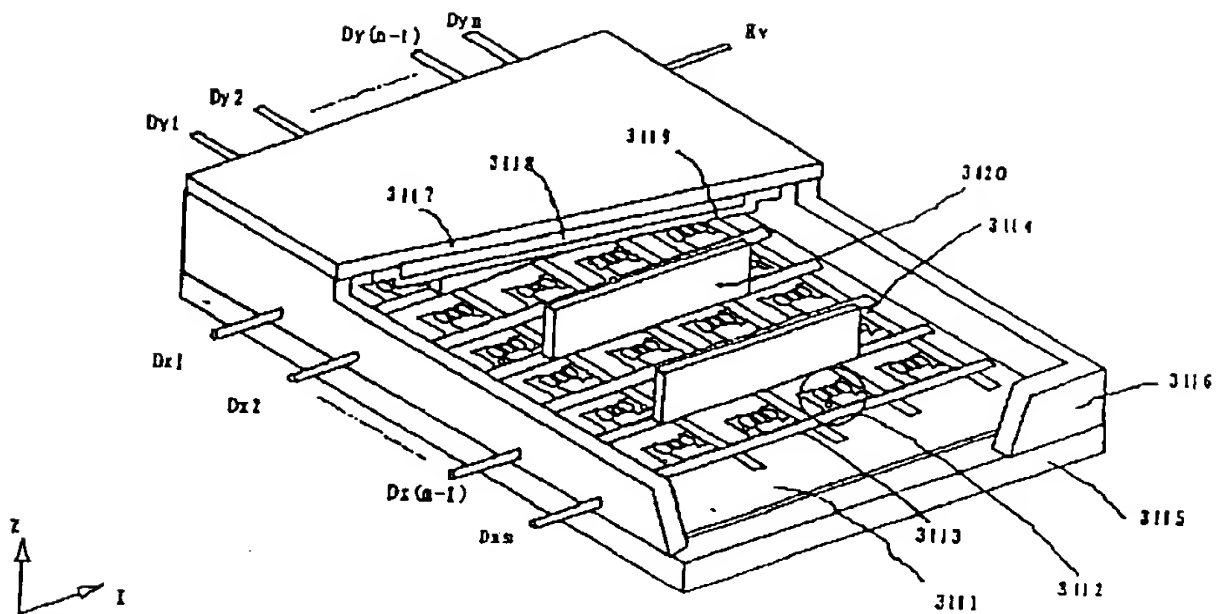
009120" 2950560

图 28



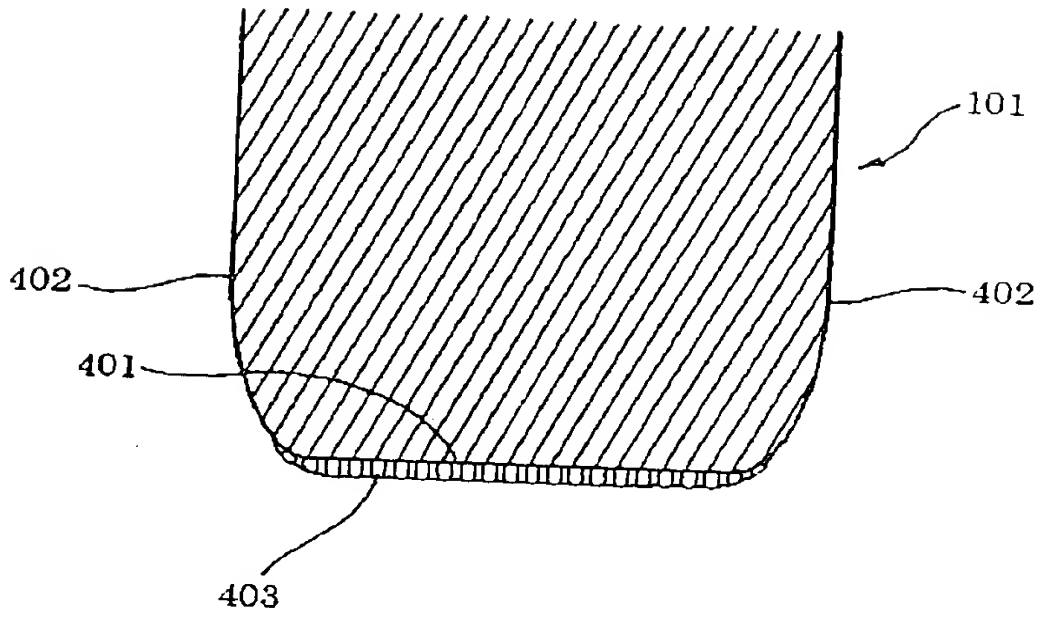
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图 30



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